

IN THE CLAIMS

Please add claims 26-31 as follows:

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B-1 D-7
26. (New) A wafer, comprising:

a substrate;

a porous layer comprised of a nanoporous material deposited on the substrate, the porous layer including a low density portion closer to the substrate than a high density portion, the high density portion being a densified form of the low density portion; and

a cap layer deposited on the porous layer in contact with the high density portion, the cap layer including an oxide-based material.

27. (New) The wafer of claim 26, wherein the cap layer includes a Plasma Enhanced Chemical Vapor Deposition (PECVD) oxide layer.

28. (New) An apparatus, comprising:

a deposition chamber;

a wafer positioned in the deposition chamber, the wafer including:

a substrate;

a porous layer comprised of a nanoporous material deposited on the substrate, the porous layer including a low density portion closer to the substrate than a high density portion, the high density portion being a densified form of the low density portion; and

a cap layer deposited on the porous layer in contact with the high density portion,
the cap layer including an oxide-based material; and

a plasma generator operable to generate a plasma within the deposition chamber to
provide the densified form of the low density portion of the porous layer.

29. (New) The apparatus of claim 28, wherein the cap layer includes a Plasma Enhanced
Chemical Vapor Deposition (PECVD) oxide layer.

30. (New) The apparatus of claim 28, wherein the plasma generator includes means for
generating a high density plasma stream of Argon ions.

31. (New) The wafer of claim 10, wherein the porous material is a nanoglass and the second
portion is a densified form of the first portion.